

Electronic Supplementary Information for

Evidence of intrinsic ambipolar charge transport in a high band gap organic semiconductor

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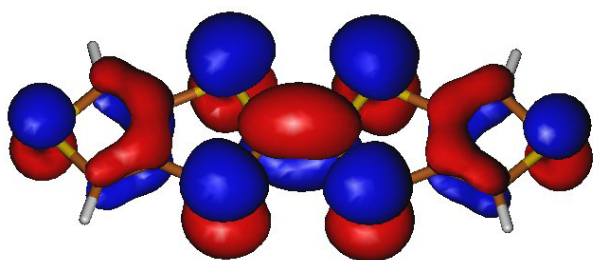


Figure S1. HOMO of the isolated planar DT-TTF molecule

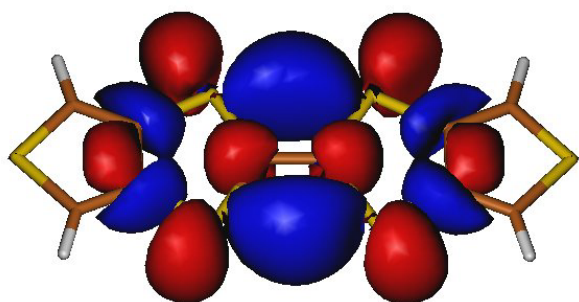


Figure S2. LUMO of the isolated planar DT-TTF molecule

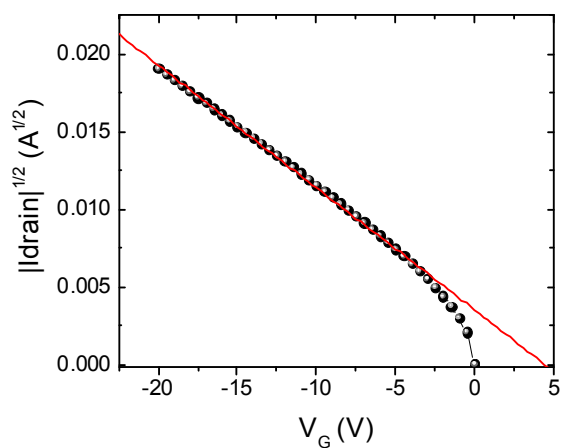


Figure S3. Square-root of drain current (I_D) as a function of gate bias (V_G) in the saturation regime ($V_G = V_D$) and fit (solid line) used to extract hole mobility.

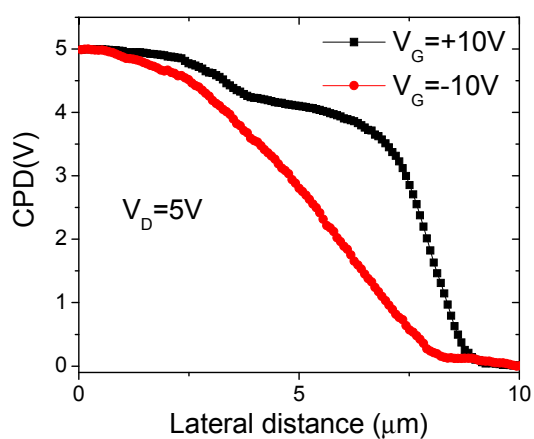


Figure S4. Contact potential difference profiles crossing the transistor channel for gate bias $+10V$ and $-10V$ at drain bias $V_D = 5V$.

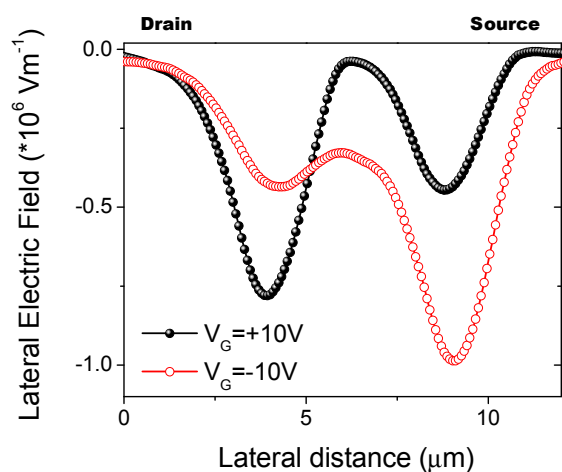


Figure S5. Lateral electric field versus distance across the source-drain gap at positive and negative gate voltages.